



US 20240213243A1

(19) **United States**

(12) **Patent Application Publication**  
**Katakam et al.**

(10) **Pub. No.: US 2024/0213243 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **FORK SHEET DEVICE WITH WRAPPED  
SOURCE AND DRAIN CONTACT TO  
PREVENT NFET TO PFET CONTACT  
SHORTAGE IN A TIGHT SPACE**

*H01L 23/522* (2006.01)

*H01L 29/08* (2006.01)

*H01L 29/66* (2006.01)

(52) **U.S. Cl.**

CPC ..... *H01L 27/092* (2013.01); *H01L 23/50*  
(2013.01); *H01L 23/5226* (2013.01); *H01L*  
*29/0847* (2013.01); *H01L 29/66477* (2013.01)

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(21) Appl. No.: **18/145,003**

(22) Filed: **Dec. 21, 2022**

**Publication Classification**

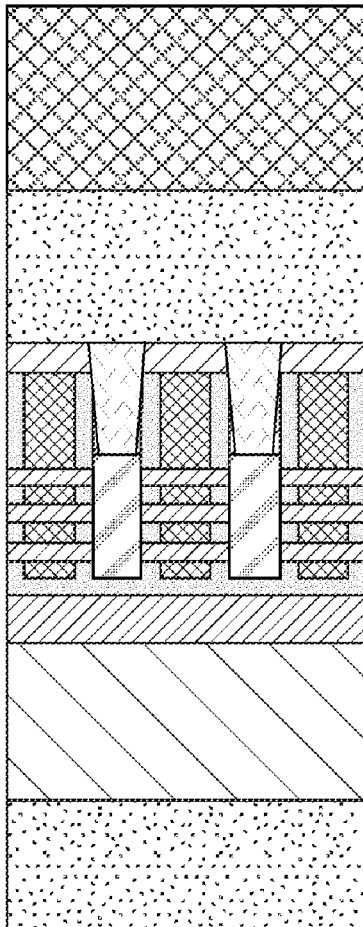
(51) **Int. Cl.**  
*H01L 27/092* (2006.01)  
*H01L 23/50* (2006.01)

(57)

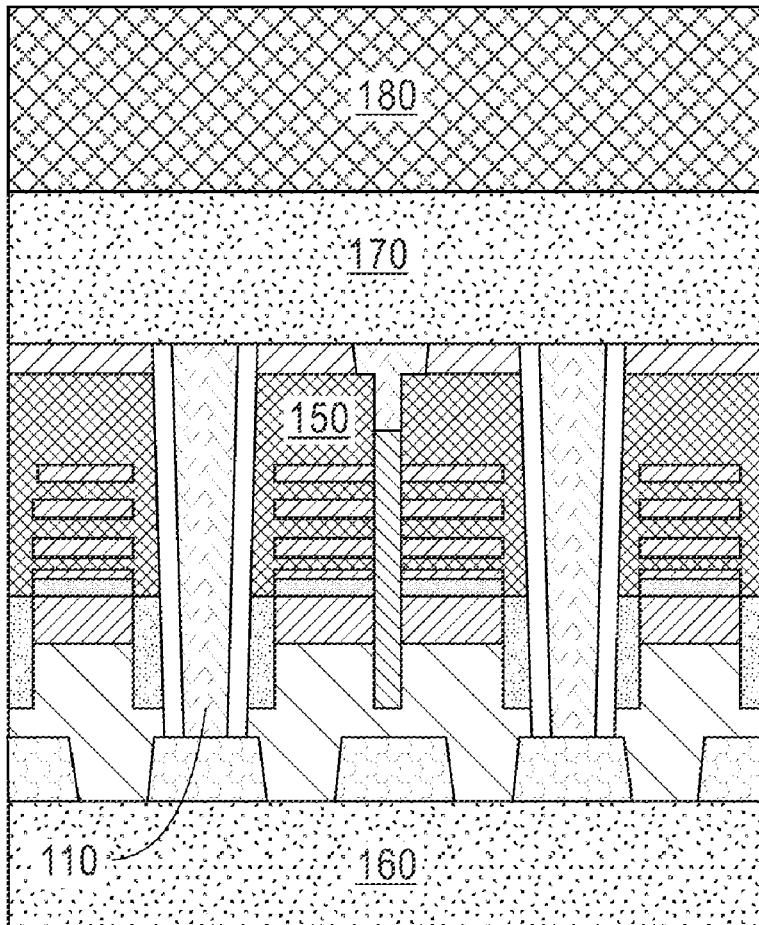
**ABSTRACT**

A microelectronic device includes a first source and drain structure adjacent to a second source and drain structure. A first conductive contact is in contact with a top surface and side surface of the first source and drain structure. A second conductive contact is in contact with a top surface and side surface of the second source and drain structure. The second conductive contact includes a via extension to connect to a backside component. A separating layer is located between the first conductive contact and the second conductive contact. A first sidewall of the separating layer is flush with the first conductive contact. A second sidewall of the separating layer is flush with the second conductive contact.

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Section X



Section Y2